

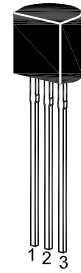
2SC930

NPN Silicon Epitaxial Planar Transistor

for FM RF amp, mixer, osc, converter and IF amplifier.

The transistor is subdivided into four groups C, D, E and F, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	30	mA
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at V _{CE} = 6 V, I _C = 1 mA	Current Gain Group					
	C	h _{FE}	40	-	80	-
	D	h _{FE}	60	-	120	-
	E	h _{FE}	100	-	200	-
	F	h _{FE}	160	-	320	-
Collector Base Cutoff Current at V _{CB} = 10 V	I _{CBO}	-	-	1	μA	
Emitter Base Cutoff Current at V _{EB} = 4 V	I _{EBO}	-	-	1	μA	
Gain Bandwidth Product at V _{CE} = 6 V, I _C = 1 mA	f _T	-	300	-	MHz	
Reverse Transfer Capacitance at V _{CB} = 6 V, f = 1 MHz	C _{re}	-	-	1.8	pF	
Turn-on Time at V _{IN} = +12 V, V _{BE} = -3 V,appointed circuit	t _{on}	-	30	-	ns	
Turn-off Time at V _{IN} = -12 V, V _{BE} = +3 V, appointed circuit	t _{off}	-	30	-	ns	

